



Preliminary Information DPF2100P45A0052

Press-Pack FRD

DS6217-2 July 2018 (LN35908)

FEATURES

- Low reverse recovery charge
- · High switching speed
- Low forward voltage drop
- Outstanding thermal cycling capability
- All-FRD configuration
- High tolerance of non-uniform clamping pressure

APPLICATIONS

- High voltage DC transmission
- Flexible AC transmission systems
- High reliability inverters
- Motor controllers

ORDERING INFORMATION

Order As:

DPF2100P45A0052

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{RRM}		4500V
V_{F}	(typ)	2.4V
I _F	(max)	2100A
I _{FM}	(max)	4200A

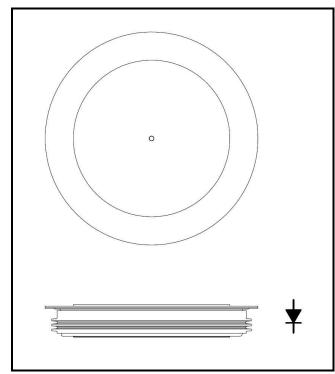


Fig.1 Circuit configuration



Fig. 2 Package



ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{RRM}	Repetitive peak reverse voltage		4500	V
I _F	Forward current	T _{case} = 105°C	2100	А
I _{FM}	Max. forward current	1ms, T _j = 125°C	4200	А
P _{max}	Max. power dissipation	$T_{case} = 25^{\circ}C, T_{j} = 125^{\circ}C$	22.7	kW
I _{FSM}	Surge (non-repetitive) on-state current	10ms half-sine, T _{case} =125°C, V _R =0V	40.8	kA

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
R _{th(j-c)} *	Thermal resistance – junction to case (cathode side)	DC	-	0.0044	°C/W
R _{th(c-h)} *	Thermal resistance – case to heatsink (cathode side)	Clamping force 70kN (with mounting compound)	-	0.0018	°C/W
T _{vj}	Virtual junction temperature	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	125	°C
F _m	Clamping force	-	65	75	kN

Note:

Heat transfer occurs primarily through the cathode side of the device.



ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
I _{RM}	Collector cut-off current	$V_R = V_{RRM}$			5	mA
		$V_R = V_{RRM}, T_{case} = 125$ °C		30	90	mA
V _F	Diode forward voltage	I _F = 2100A, T _j = 25°C		2.4		V
		I _F = 2100A, T _j = 125°C		2.1		V

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
Q _{rr}	Diode reverse recovery charge	$I_F = 2100A$ $V_R = 2800V$		2500		μC
I _{rr}	Diode reverse recovery current	$dI_F/dt = 5000A/\mu s$		2300		Α
E _{rec}	Diode reverse recovery energy	Tested with IGBT device Dynex DPI2100P45A5200		4300		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Тур.	Max	Units
Q _{rr}	Diode reverse recovery charge	$I_F = 2100A$ $V_R = 2800V$		4900		μC
I _{rr}	Diode reverse recovery current	$dI_F/dt = 5000A/\mu s$		2900		Α
E _{rec}	Diode reverse recovery energy	Tested with IGBT device Dynex DPI2100P45A5200		8800		mJ



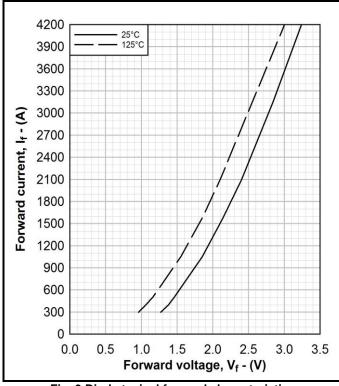


Fig. 3 Diode typical forward characteristics

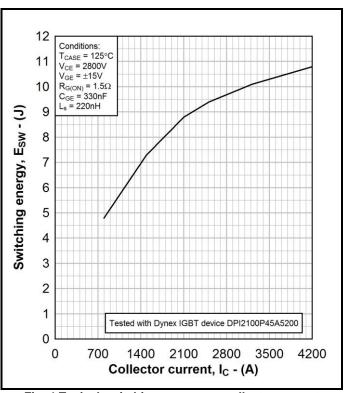


Fig. 4 Typical switching energy vs. collector current

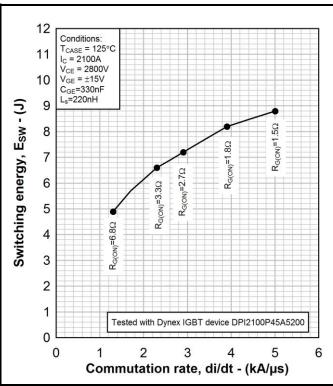


Fig. 5 Typical switching energy vs. gate resistance

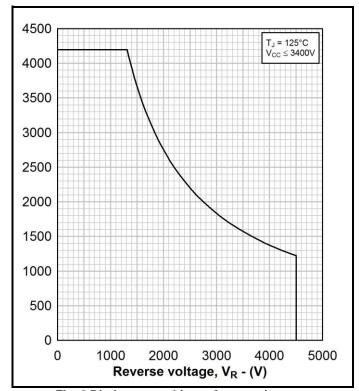


Fig. 6 Diode reverse bias safe operating area



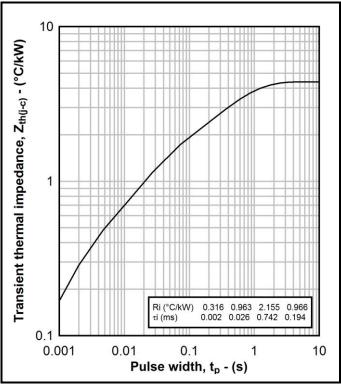


Fig. 7 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.

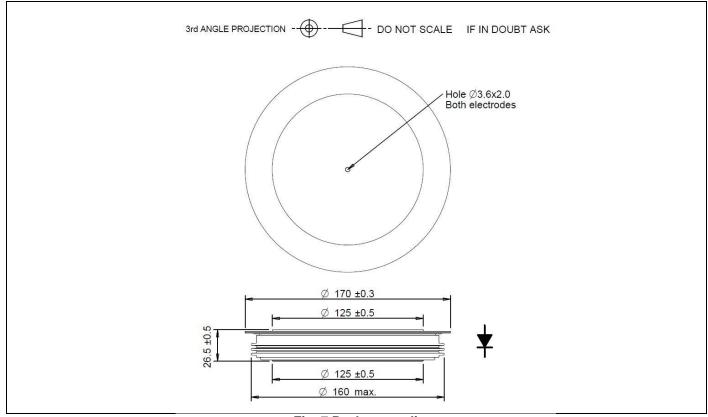


Fig. 7 Package outline



IMPORTANT INFORMATION:

This publication is provided for information only and not for resale.

The products and information in this publication are intended for use by appropriately trained technical personnel.

Due to the diversity of product applications, the information contained herein is provided as a general guide only and does not constitute any guarantee of suitability for use in a specific application. The user must evaluate the suitability of the product and the completeness of the product data for the application. The user is responsible for product selection and ensuring all safety and any warning requirements are met. Should additional product information be needed please contact Customer Service.

Although we have endeavoured to carefully compile the information in this publication it may contain inaccuracies or typographical errors. The information is provided without any warranty or guarantee of any kind.

This publication is an uncontrolled document and is subject to change without notice. When referring to it please ensure that it is the most up to date version and has not been superseded.

The products are not intended for use in applications where a failure or malfunction may cause loss of life, injury or damage to property. The user must ensure that appropriate safety precautions are taken to prevent or mitigate the consequences of a product failure or malfunction.

The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

Product Status & Product Ordering:

We annotate datasheets in the top right hand corner of the front page, to indicate product status if it is not yet fully approved for production. The annotations are as follows:-

Target Information: This is the most tentative form of information and represents a very preliminary specification.

No actual design work on the product has been started.

The product design is complete and final characterisation for volume production is in progress. **Preliminary Information:**

The datasheet represents the product as it is now understood but details may change.

No Annotation: The product has been approved for production and unless otherwise notified by Dynex any

product ordered will be supplied to the current version of the data sheet prevailing at the

time of our order acknowledgement.

All products and materials are sold and services provided subject to Dynex's conditions of sale, which are available on request.

Any brand names and product names used in this publication are trademarks, registered trademarks or trade names of their respective owners.

HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln, Lincolnshire, LN6 3LF,

United Kingdom

+44(0)1522 500550 +44(0)1522 500500

Web: http://www.dynexsemi.com

CUSTOMER SERVICE

DYNEX SEMICONDUCTOR LTD

Doddington Road, Lincoln, Lincolnshire, LN6 3LF, United Kingdom

Fax: +44(0)1522 500020

Tel: +44(0)1522 502753 / 502901 Email: Power_solutions@dynexsemi.com

Technical Documentation - Not for resale. © Dynex Semiconductor Ltd. 2017

Fax:

Tel: